

Process		NR71 3000P
Dehydration Bake (hot plate)	temp (°C)	200
	time (min)	5
Spin coating NR71- 3000P	Speed/acc (rpm)	300
	time (s)	3
	speed (rpm)	3000
	acceleration (rpm/s)	5000
	time (s)	45
Soft-bake (hotplate)	temp (°C)	150
	time (s)	60
Expose (12mW/cm <sup>2</sup> )	mode	HC
	time (s)	20
Post Exposure Bake (hot plate)	temp (°C)	100
	time (s)	60
Develop	developer	RD 6
	developer: di water ratio	No mix
	time (sec) (approx.)	25 – 30 sec
Rinse in DI water	time (min)	2

**NB:**

1. SC: Soft Contact; HC: Hard Contact; VC: Vacuum Contact; LVC: Low Vacuum Contact
2. Development of NR71-3000P is accomplished in a basic water solution (RD6)
3. If exposure is insufficient, bleaching within the exposed areas will be observed after development. This should not happen with sufficiently exposed resist surface which should be fully cross-linked.
4. NR71-3000P DOES NOT dissolve well in acetone. Use RR41 Stripper for removal.
5. These are results using a bare Silicon substrate. Films on substrates and/or the use of other types of substrates may affect the exposure and/or development time. Adjust as needed.
6. Use of this process data should act as a guide to developing and/or refining your process rather than being adopted as is. The process was used to resolve a minimum feature size of 10 µm.
7. FYI - At 5,000 rpm spins, develop was accomplished within 24 sec. At 2000 rpm, develop was accomplished in 38 sec. Exposure in both cases is 20 Sec.